

ISC5804AT2

Low frequency Application
Silicon NPN Epitaxial Type

DESCRIPTION

2SC5804 is a super mini package resin sealed silicon NPN epitaxial transistor, It is designed for low frequency application. Since it is a super-thin flat lead type package, a high-density mounting are possible. Complementary with 2SC3052.

FEATURE

- Super-thin flat lead type package. $t=0.45\text{mm}$
- Excellent linearity of DC forward current gain.
- Low collector to emitter saturation voltage
 $V_{CE(sat)}=0.3\text{V max (@}I_C=100\text{mA}/I_B=10\text{mA)}$

APPLICATION

For hybrid IC, small type machine low frequency voltage amplify application.

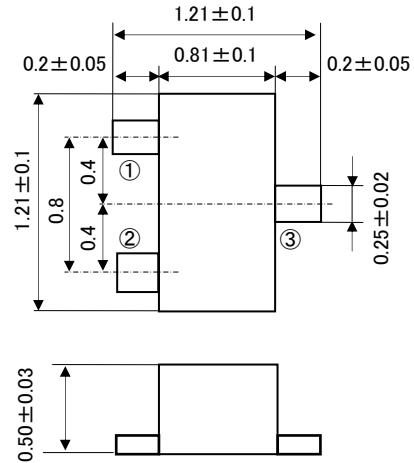
MAXIMUM RATING($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	RATING	UNIT
VCBO	Collector to Base voltage	50	V
VEBO	Emitter to Base voltage	6	V
VCEO	Collector to Emitter voltage	50	V
IC	Collector current	150	mA
PC	Collector dissipation($T_a=25^\circ\text{C}$)	150(*)	mW
Tj	Junction temperature	+125	$^\circ\text{C}$
Tstg	Storage temperature	-55 ~ +125	$^\circ\text{C}$

*package mounted on 9mm x 19mm x 1mm glass-epoxy substrate.

OUTLINE DRAWING

Unit: mm



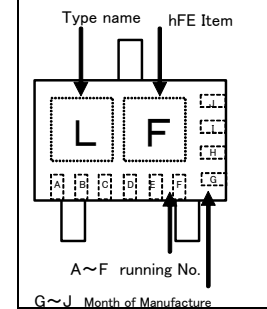
※The dimension tolerance is reference value.

JEITA:

Terminal Connector

- ①: Base
- ②: Emitter
- ③: Collector

Equivalent circuit



ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$)

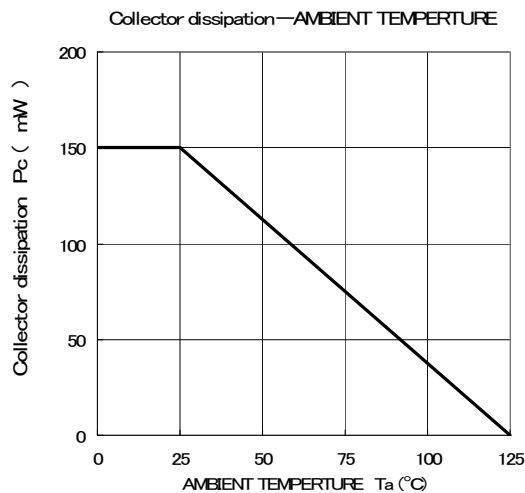
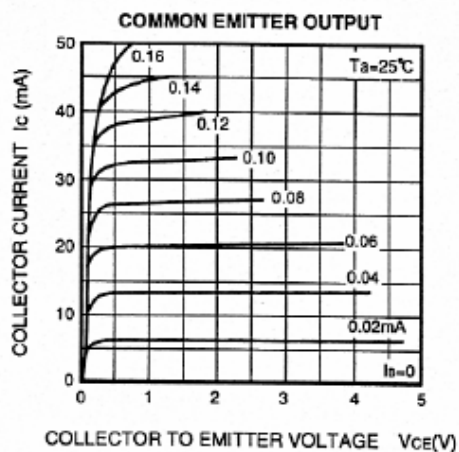
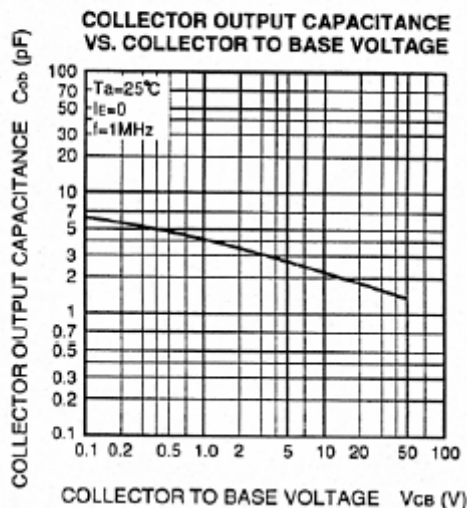
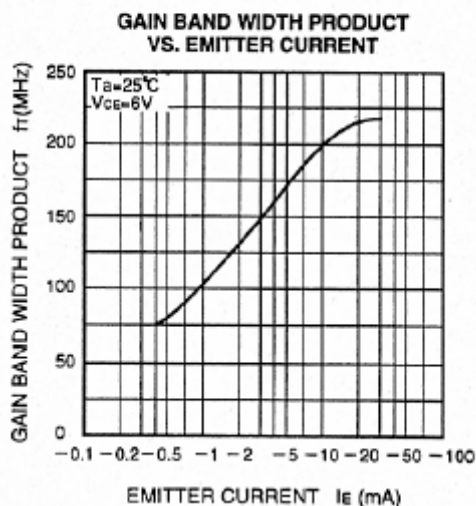
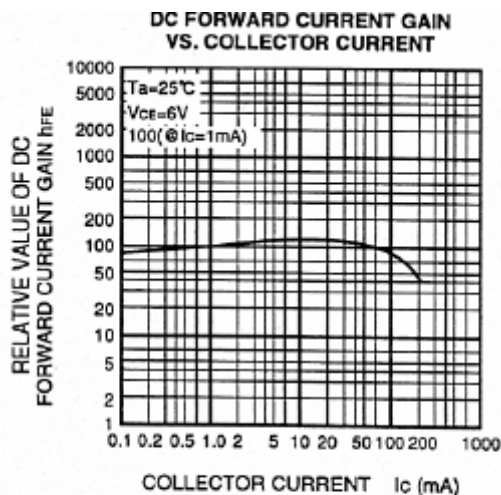
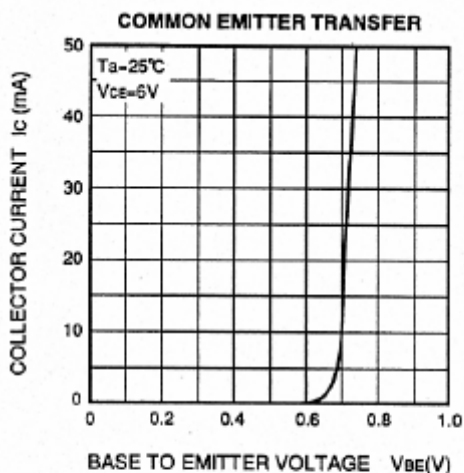
SYMBOL	PARAMETER	TEST CONDITION	LIMIT			UNIT TYP
			MIN	TYP	MIN	
Collector to Emitter Breakdown voltage	$V_{(BR)CEO}$	$I_C=100\ \mu\text{A}, R_{BE}=\infty$	50	—	—	V
Collector cut off current	I_{CBO}	$V_{CB}=50\text{V}, I_E=0\text{mA}$	—	—	0.1	μA
Emitter cut off current	I_{EBO}	$V_{EB}=6\text{V}, I_C=0\text{mA}$	—	—	0.1	μA
DC forward current gain	hFE	$V_{CE}=6\text{V}, I_C=1\text{mA}$	150	※	800	—
DC forward current gain	hFE	$V_{CE}=6\text{V}, I_C=0.1\text{mA}$	90	—	—	—
C to E saturation voltage	$V_{CE(sat)}$	$I_C=100\text{mA}, I_B=10\text{mA}$	—	—	0.3	v
Gain bandwidth product	fT	$V_{CE}=6\text{V}, I_E=-10\text{mA}$	—	200	—	MHz
Collector output capacitance	Cob	$V_{CB}=6\text{V}, I_E=0\text{mA}, f=1\text{MHz}$	—	2.5	—	pF
Noise figure	NF	$V_{CE}=6\text{V}, I_E=-0.1\text{mA}, f=1\text{kHz}, R_G=2\text{k}\Omega$	—	—	15	dB

※ It shows hFE classification in below table.

Item	E	F	G
hFE	150~300	250~500	400~800

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